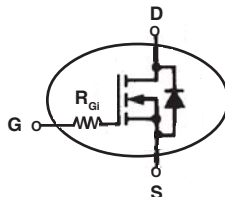


Linear L2™ Power MOSFET w/ Extended FBSOA

IXTT44N25L2HV IXTH44N25L2

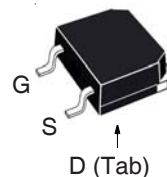
$$\begin{aligned} V_{DSS} &= 250V \\ I_{D25} &= 44A \\ R_{DS(on)} &\leq 75m\Omega \end{aligned}$$

N-Channel Enhancement Mode

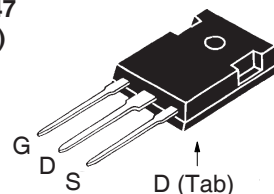


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	250	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$	250	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	44	A
I_{DM}	$T_C = 25^\circ\text{C}, \text{Pulse Width Limited by } T_{JM}$	120	A
I_A	$T_C = 25^\circ\text{C}$	22	A
E_{AS}	$T_C = 25^\circ\text{C}$	3	J
P_D	$T_C = 25^\circ\text{C}$	400	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in
Weight	TO-268HV	4	g
	TO-247	6	g

TO-268HV
(IXTT..HV)



TO-247
(IXTH)



G = Gate D = Drain
S = Source Tab = Drain

Features

- Designed for Linear Operation
- International Standard Packages
- Avalanche Rated
- Guaranteed FBSOA at 75°C

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Solid State Circuit Breakers
- Soft Start Controls
- Linear Amplifiers
- Programmable Loads
- Current Regulators

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	250		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			10 μA 75 μA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.5 \cdot I_{D25}, \text{Note 1}$			75 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	11	18	25 S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		5740	pF
C_{oss}			820	pF
C_{rss}			245	pF
R_{Gi}	Integrated Gate Input Resistor		3.3	Ω
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 0\Omega$ (External)		30	ns
t_r			78	ns
$t_{d(off)}$			110	ns
t_f			32	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		256	nC
Q_{gs}			40	nC
Q_{gd}			146	nC
R_{thJC}	TO-247			0.31 $^\circ\text{C/W}$
R_{thCS}			0.21	$^\circ\text{C/W}$

Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 250\text{V}$, $I_D = 0.96\text{A}$, $T_C = 75^\circ\text{C}$, $T_p = 2\text{s}$	240		W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			44 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			176 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	$I_F = 22\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		366	ns
Q_{RM}			4.9	μC
I_{RM}			26.6	A

Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

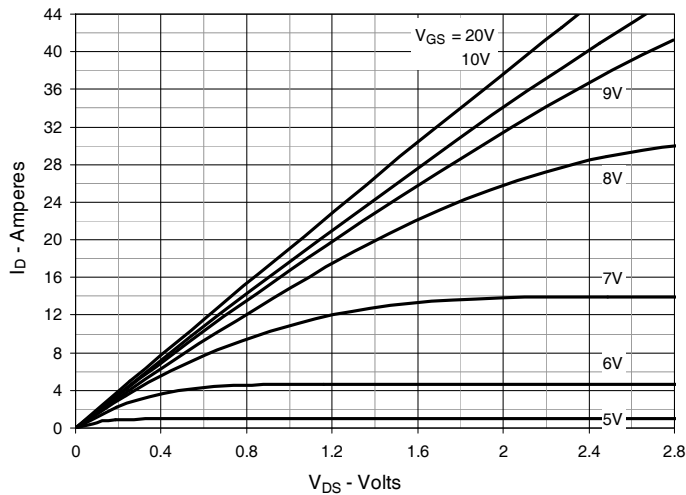


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

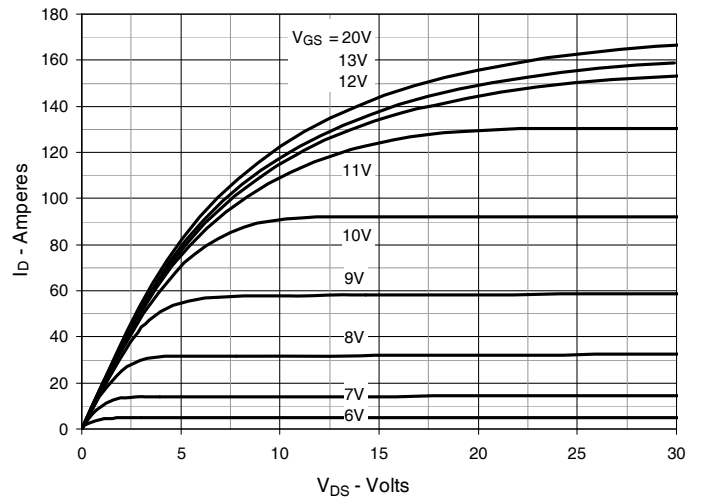


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

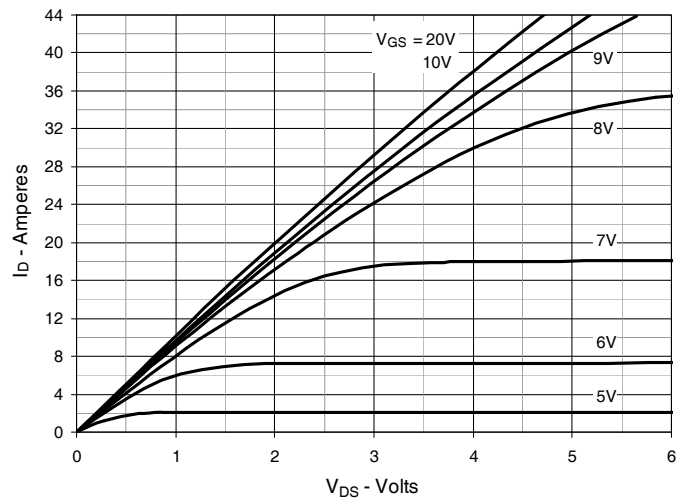


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 22\text{A}$ Value vs. Junction Temperature

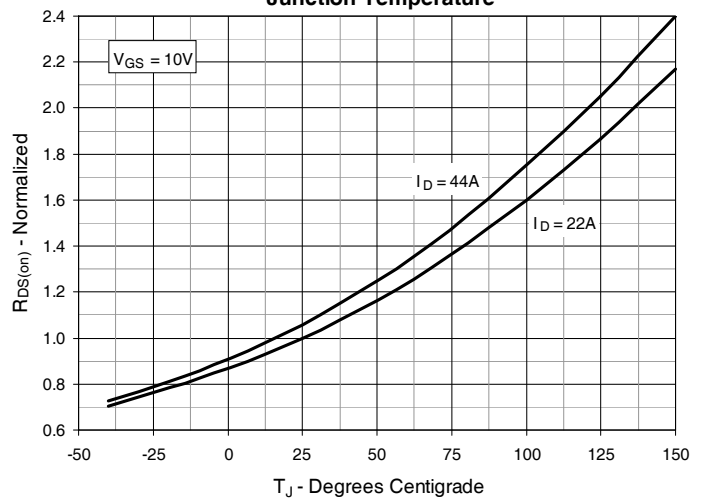


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 22\text{A}$ Value vs. Drain Current

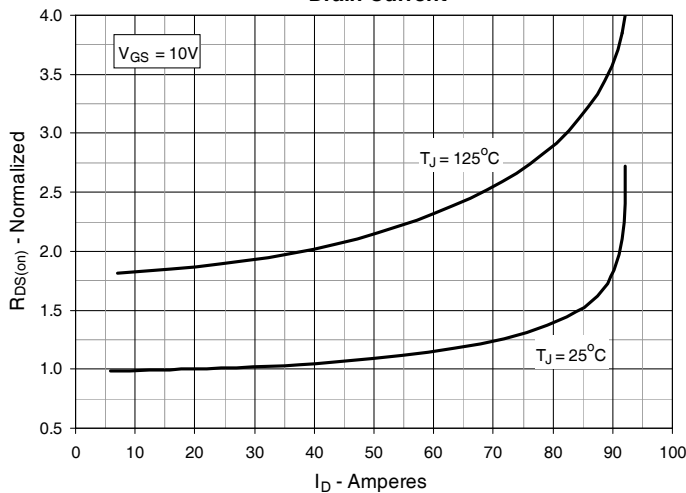


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

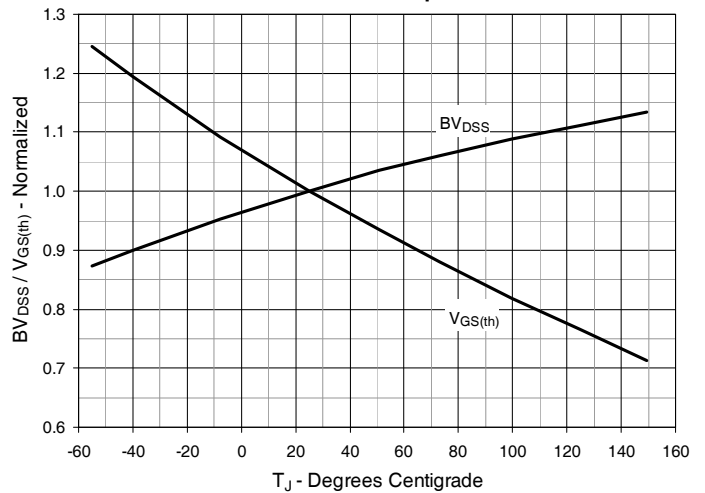


Fig. 7. Maximum Drain Current vs. Case Temperature

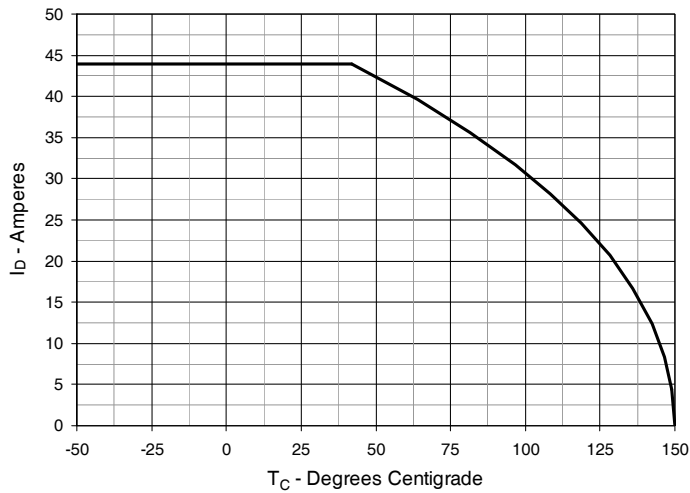


Fig. 8. Input Admittance

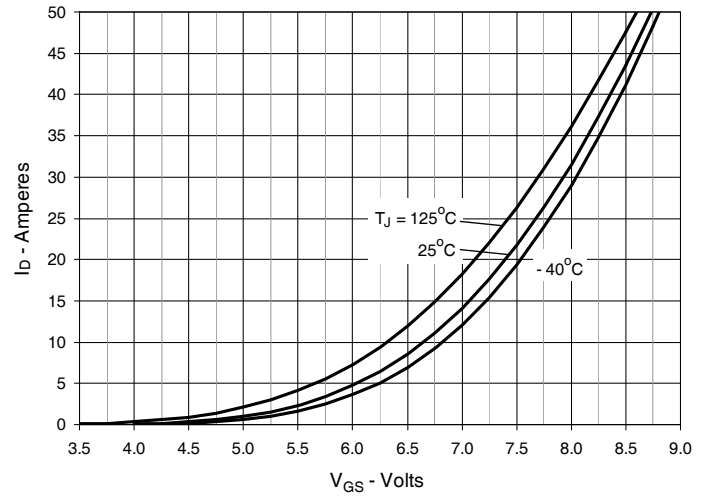


Fig. 9. Transconductance

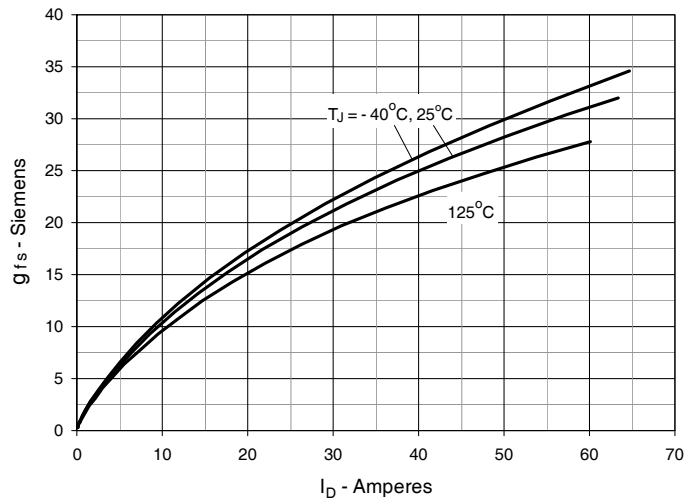


Fig. 10. Forward Voltage Drop of Intrinsic Diode

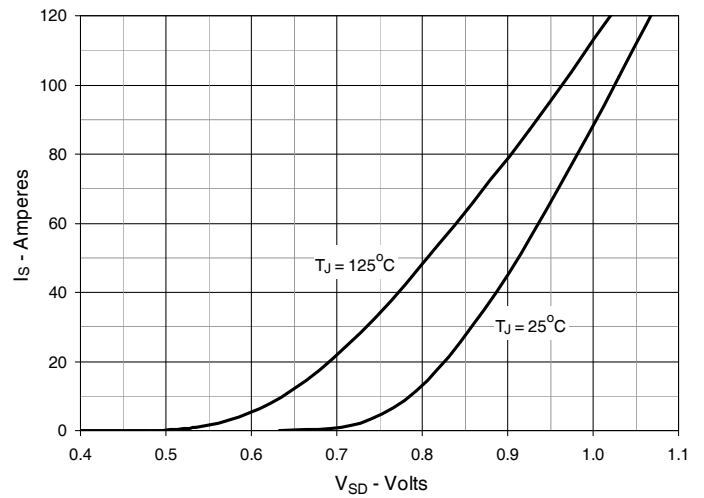


Fig. 11. Gate Charge

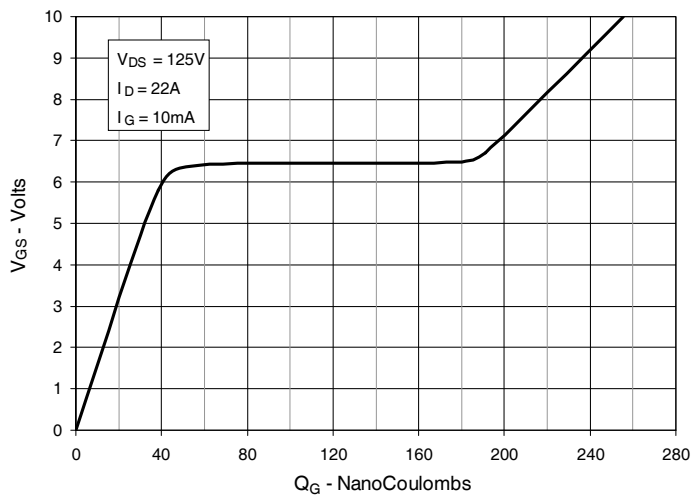


Fig. 12. Capacitance

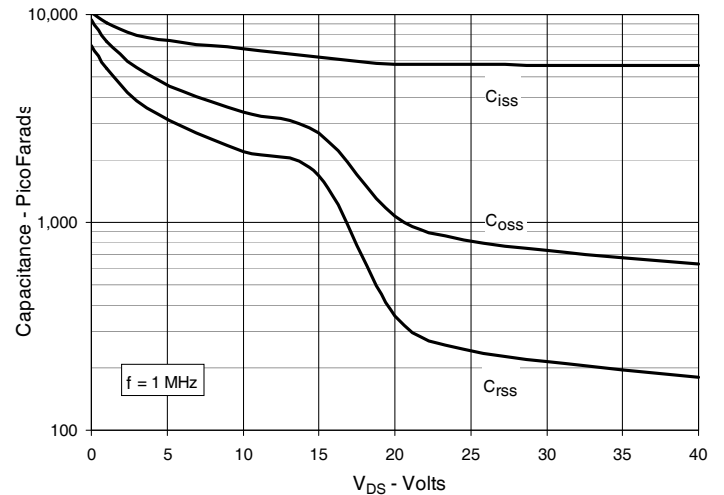


Fig. 13. Forward-Bias Safe Operating Area

@ $T_C = 25^\circ\text{C}$

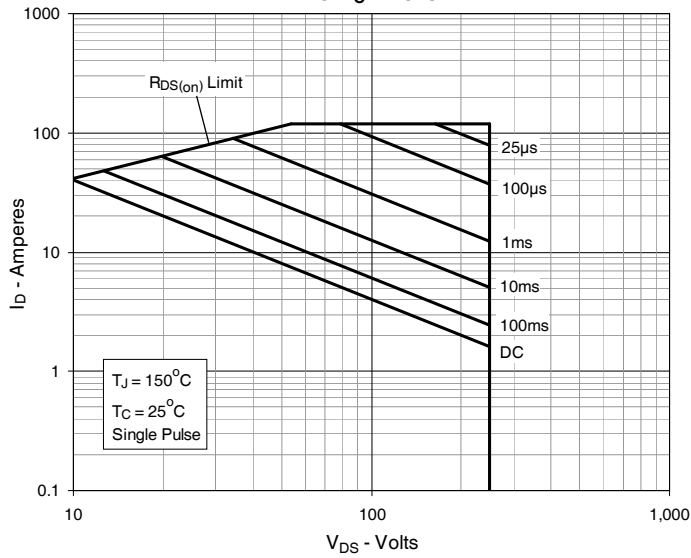


Fig. 14. Forward-Bias Safe Operating Area

@ $T_C = 75^\circ\text{C}$

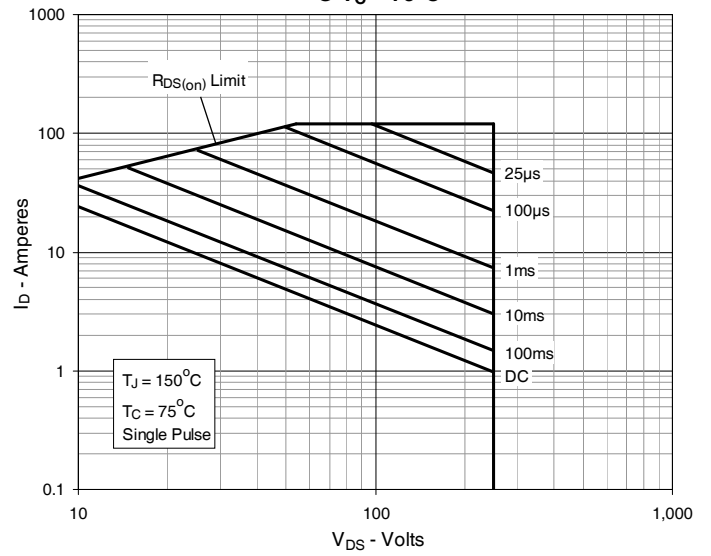
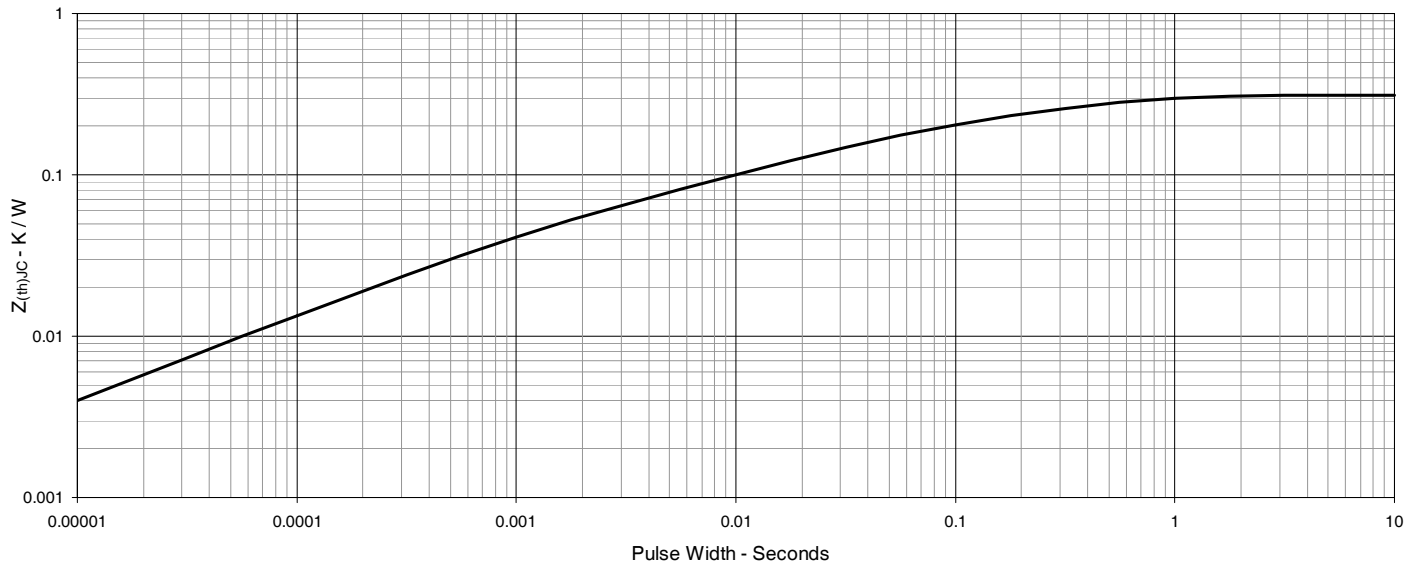
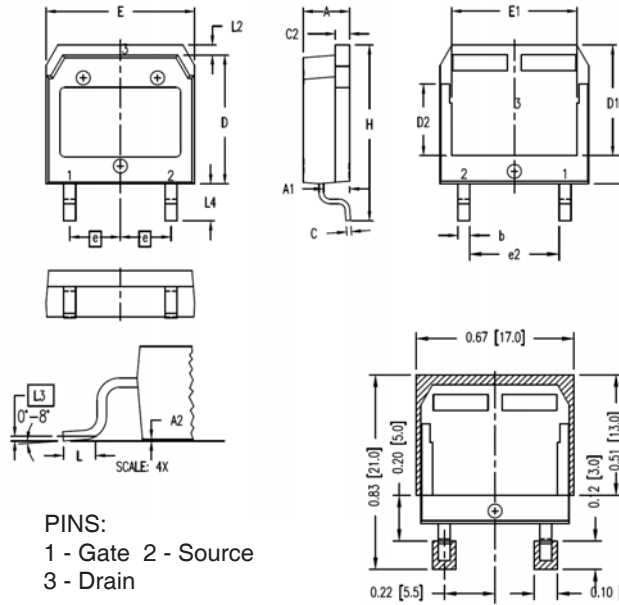


Fig. 15. Maximum Transient Thermal Impedance

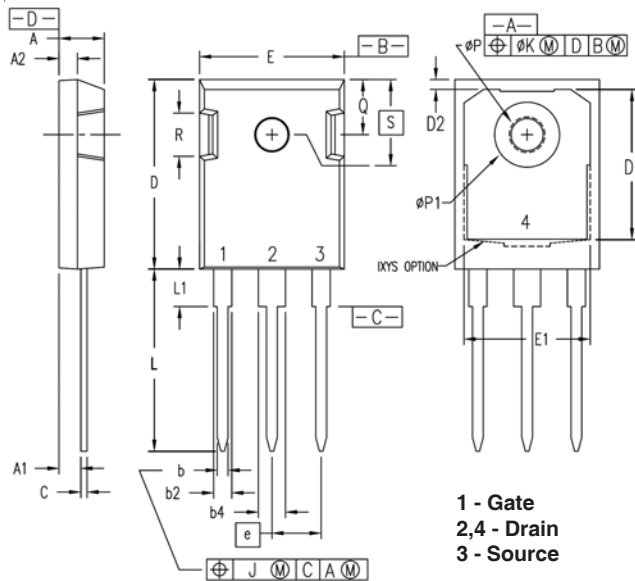


TO-268HV Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
(e2)	.374	.386	9.50	9.80
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

TO-247 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215	BSC	5.45	BSC
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
øP	.140	.144	3.55	3.65
øP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242	BSC	6.15	BSC

